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# 2SC2462

Silicon NPN Epitaxial

# HITACHI

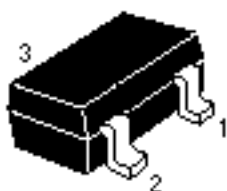
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## Application

Low frequency amplifier

## Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

## 2SC2462

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	50	V
Collector to emitter voltage	$V_{CEO}$	40	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Emitter current	$I_E$	−100	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	−55 to +150	°C

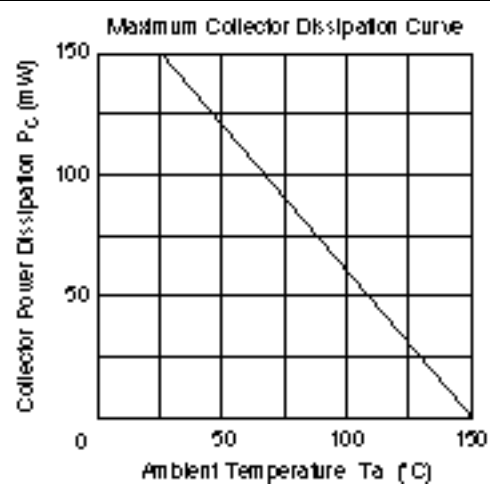
### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	40	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 30 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	100	—	500		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$

Note: 1. The 2SC2462 is grouped by  $h_{FE}$  as follows.

Grade	B	C	D
Mark	LB	LC	LD
$h_{FE}$	100 to 200	160 to 320	250 to 500

See characteristic curves of 2SC458 (LG).



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# HITACHI

## **Hitachi, Ltd.**

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

**Hitachi America, Ltd.**

Semiconductor & IC Div.

2000 Sierra Point Parkway

Brisbane, CA 94005-4835

U.S.A.

Tel 415-589-8300

Fax 415-583-4207

**Hitachi Europe GmbH**

Electronic Components Group

Continental Europe

Danrecker Straße 3

D-85622 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

**Hitachi Europe Ltd.**

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

Maidenhead

Berkshire SL6 6YA

United Kingdom

Tel 0628-885000

Fax 0628-778322

**Hitachi Asia Pte. Ltd.**

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0404

Tel 535-2100

Fax 535-1533

**Hitachi Asia (Hong Kong) Ltd.**

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074